



## <sup>40</sup>ĪN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT:	Hiroji Kawai	)	Attorney Docket No: 09792909-4785
		)	
SERIAL NO.	09/768,912	)	GROUP ART UNIT: 2812
FILING DATE:	January 21, 2001	)	EXAMINER: Unknown
TITLE: "SEMICONDUCTOR DEVICE AND ITS MANUFACTURING METHOD		)	

## AMENDMENT "B" BEFORE FIRST OFFICE ACTION

Asst. Commissioner of Patents Washington, D.C. 20231

In the above identified patent application, amend the following application as follows:

## IN THE ABSTRACT OF THE DISCLOSURE

Please cancel the Abstract of the Disclosure and substitute the following Abstract of the Disclosure therefor:

G<sub>I</sub> --A semiconductor device having a single-crystal substrate made of a material different from nitride III-V compound semiconductors, and a device made on one major surface of said single-crystal substrate by using III-V compound semiconductors, including electrical connection to said device being made through a via hole formed in said single-crystal substrate and method of making the same.--

## REMARKS

The foregoing amendment is presented in response to the Notice of Corrected Application dated May 22, 2001. It is submitted that the application is now in condition for examination.

Respectfully submitted,

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